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ter Clean	ning Parameters	Deposition S	Deposition Sputtering Parameters	Deposition	Deposition Parameters
Beam)	-	(I)	(Ion Beam)	(Electron Bean	(Electron Beam Evaporation)
Argon	u	Gas type	Argon	Pressure	<1x10 ⁻⁴ Torr
2.5-3	2.5-3.5 sccm	Flow	2.5-3.5 secm	Deposition rate 3.5-3.5 Å/sec	3.5-3.5 Å/sec
1-2 keV	eV	Energy	1-3 keV	Energy	8 keV
58-6	58-65 Watts	Power	58-65 Watts	Power	2.9 kW
10-3	10-35 mA	Current	15-35 mA	Current	0.375 A
20-3(20-30 min				

FIG. 7

Sputter Cleani	ning Parameters	Deposition S	Deposition Sputtering Parameters	Deposition	Deposition Parameters
(Ion B	Beam)	ľ	(Ion Beam)	(Electron Beam Evaporation)	n Evaporation)
Gas type	Argon	Gas type	Argon	Pressure	3.5x10 ⁻⁵ Torr
Flow	2 sccm	Flow	2 sccm	Deposition rate	4-5 Å/sec
Energy	2 keV	Energy	2 keV	Energy	8 keV
Power	60 Watts	Power	80 Watts	Power	1.76 kW
Current	15 mA	Current	18 mA	Current	0.226 A
Time	20 min				-

FIG. 8

Sputter Cleanir	ning Parameters	Deposition S	Deposition Sputtering Parameters	Deposition	Deposition Parameters
(Ion Be	Beam)		(Ion Beam)	(Electron Bear	(Electron Beam Evaporation)
Gas type	Argon	Gas type	Argon	Pressure	1.2x10 ⁻⁴ Torr
Flow	3 sccm	Flow	2 sccm	Deposition rate 2-3 Å/sec	2-3 Å/sec
Energy	1 keV	Energy	1 keV	Energy	7.5 keV
Power	60 Watts	Power	60 Watts	Power	2.0 kW
Current	25 mA	Current	32 mA	Current	0.15 A
Time	30 min				

FIG 9